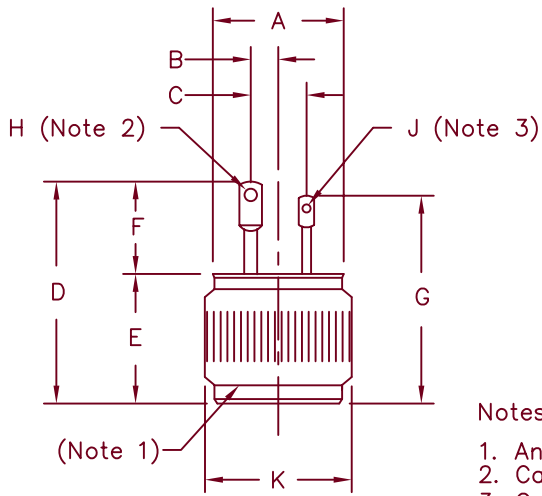


Silicon Controlled Rectifier Series 023



Notes:
 1. Anode connected to case
 2. Cathode terminal
 3. Gate terminal

	Dim. Inches		Millimeters		Notes
	Min.	Max.	Min.	Max.	
A	0.495	0.505	12.57	12.83	
B	0.068	0.080	1.73	2.03	
C	0.150	0.160	3.81	4.06	
D	0.705	0.754	17.91	19.15	
E	0.350	0.374	8.89	9.50	
F	0.345	0.380	8.76	9.65	
G	0.600	0.714	15.24	18.14	
H	0.070	0.087	1.78	2.21	Dia.
J	0.050	0.065	1.27	1.65	Dia.
K	0.500	0.503	12.54	12.78	Dia.

Microsemi Catalog Number	Forward & Reverse Repetitive Blocking	Reverse Transient Blocking
0230200L	200V	200V
0230300L	300V	300V
0230400L	400V	400V
0230500L	500V	500V
0230600L	600V	600V

- $dv/dt - 200V/\mu s$
- 300 Amperes surge current
- Low forward on-state voltage
- Economical for medium power applications
- V_{DRM} / V_{RRM} 200V to 600V

Electrical Characteristics

Max average on-state current	$I_{T(AV)23}$ 23 Amps	$T_C = 68^\circ C$ sine wave, $R_{\theta JC} = 1.65^\circ C/W$
Max peak on-state voltage	V_{FM} 1.8 Volts	$I_T = 100A; T_J = 25^\circ C$
Max holding current	I_H 80 mA	
Max peak one cycle surge current	I_{TSM} 300 A	$T_J = 125^\circ C, 8.3mS$ pulse
Max I^2t capability for fusing	I^2t 370 A^2s	$t = 8.3mS$

Thermal and Mechanical Characteristics

Storage temp range	T_{STG}	$-55^\circ C$ to $125^\circ C$
Operating junction temp range	T_J	$-55^\circ C$ to $125^\circ C$
Max thermal resistance	$R_{\theta JC}$	$1.65^\circ C/W$ junction to case
Typical thermal resistance	$R_{\theta CS}$	$1.0^\circ C/W$ case to sink
Weight		0.255 ounces (7.23 grams) typical



6 Lake Street
 Lawrence, MA 01841
 PH: (978) 620-2600
 FAX: (978) 689-0803
www.microsemi.com

04-24-07 Rev.4

Series 023

Switching

Critical rate of rise of on-state current (note 1)	di/dt	100A/usec.	$T_J = 125^\circ\text{C}$
Typical delay time (note 1)	t_d	0.5 usec.	
Typical rise time (note 1)	t_r	3.0 usec.	
Typical turn-on time	t_o	3.5 usec.	
Typical circuit commuted turn-off time (note 2)	t_q	50 usec.	$T_J = 125^\circ\text{C}$

Note 1: $I_{TM} = 20\text{A}$, $V_D = V_{DRM}$, $V_{GT} = 12\text{V}$ open circuit, 20 ohm-0.1 usec. rise time
 Note 2: $I_{TM} = 20\text{A}$, $di/dt = 5\text{A/usec.}$, $V_R = 50\text{V}$, $dv/dt = 20\text{V/usec.}$, Rated V_{DRM}

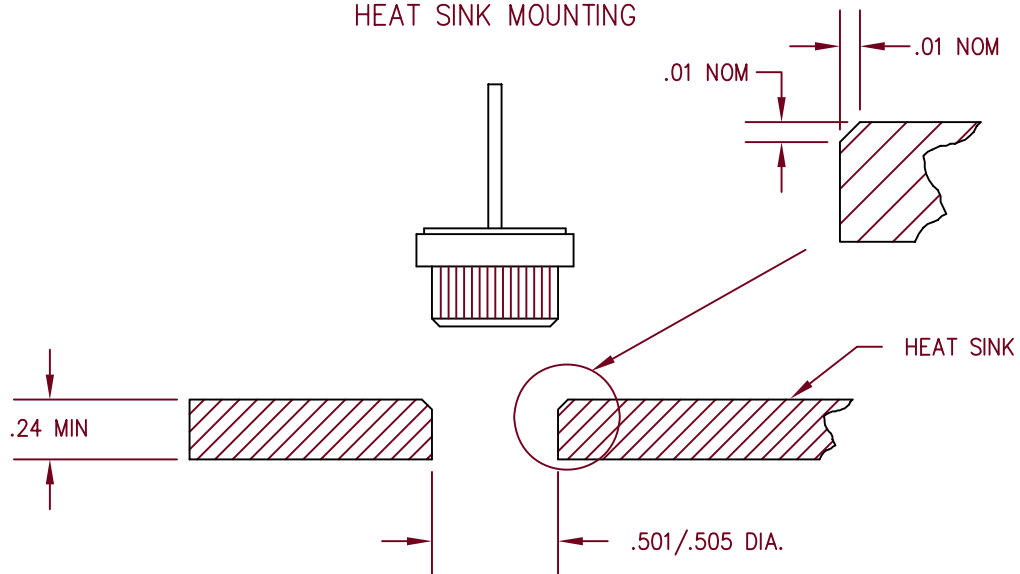
Triggering

Max. gate trigger voltage	V_{GT}	2.0V	$T_J = 125^\circ\text{C}$
Max. nontriggering gate voltage	V_{GD}	0.25V	
Max. gate trigger current	I_{GT}	40mA	
Max. peak gate power	P_{GM}	5.0W	
Average gate power	$P_{G(AV)}$	0.5W	
Max. peak gate current	I_{GM}	3.0A	
Max. peak gate voltage (forward)	V_{GM}	10.0V	
Max. peak gate voltage (reverse)	V_{GM}	5.0V	

Blocking

Max. forward leakage current	I_{DRM}	10uA	V_{DRM} , $T_J = 25^\circ\text{C}$
Max. reverse leakage current	I_{RRM}	10uA	V_{RRM} , $T_J = 25^\circ\text{C}$
Max. forward leakage current	I_{DRM}	3.0mA	V_{DRM} , $T_J = 125^\circ\text{C}$
Max. reverse leakage current	I_{RRM}	3.0mA	V_{RRM} , $T_J = 125^\circ\text{C}$
Critical rate of rise of off-state voltage	dv/dt	200V/usec.	$T_J = 125^\circ\text{C}$

HEAT SINK MOUNTING



Series 023

Figure 1
Typical Forward Characteristics

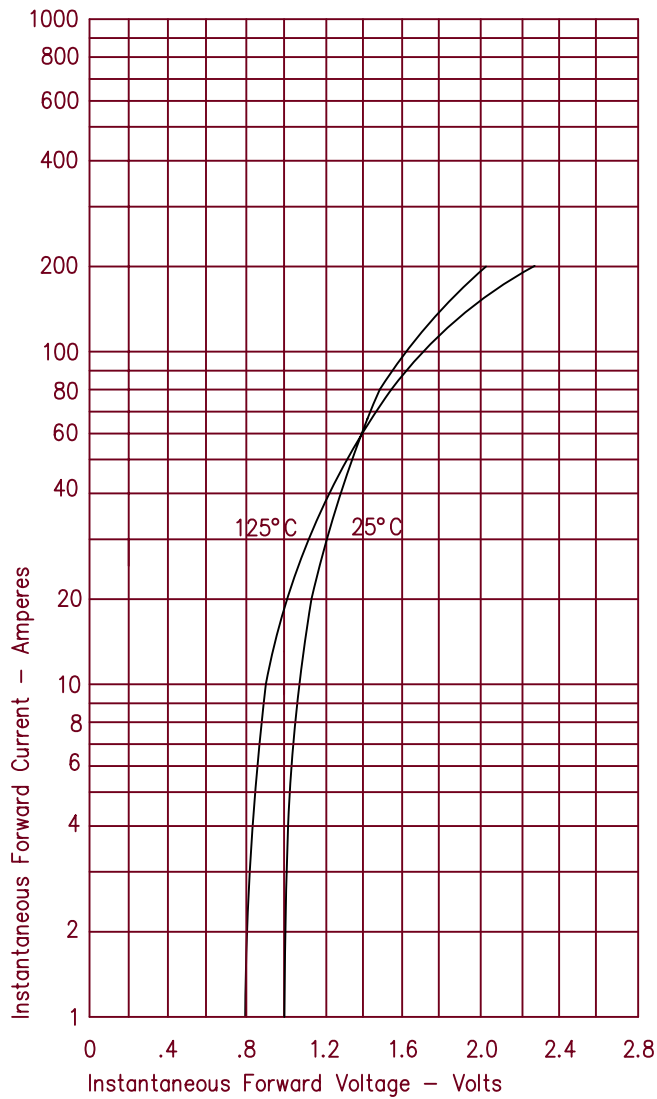


Figure 3
Maximum Forward Power Dissipation

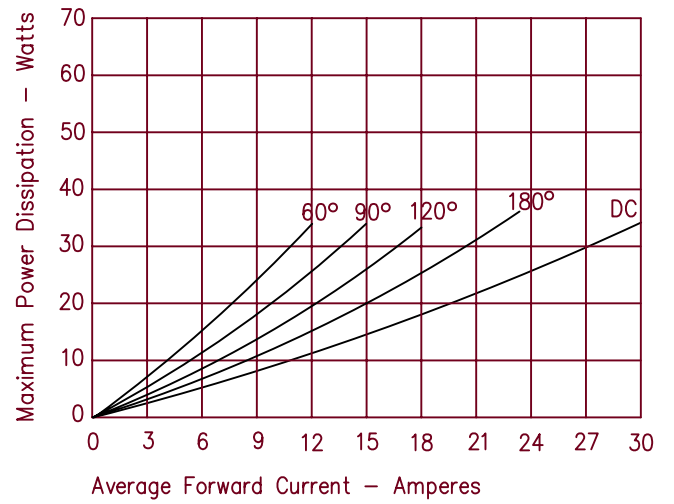


Figure 2
Forward Current Derating

